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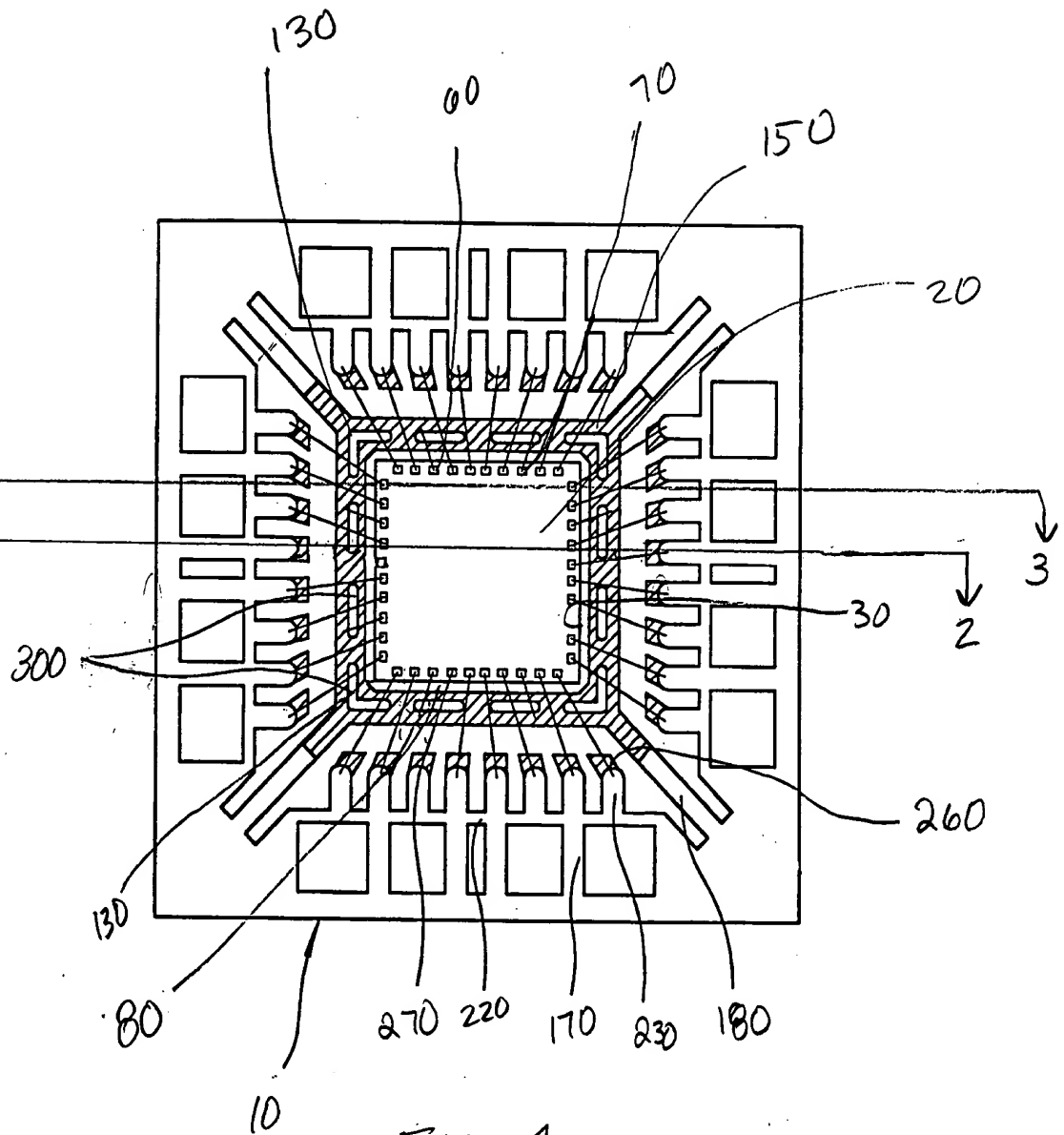
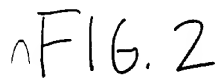


FIG. 1

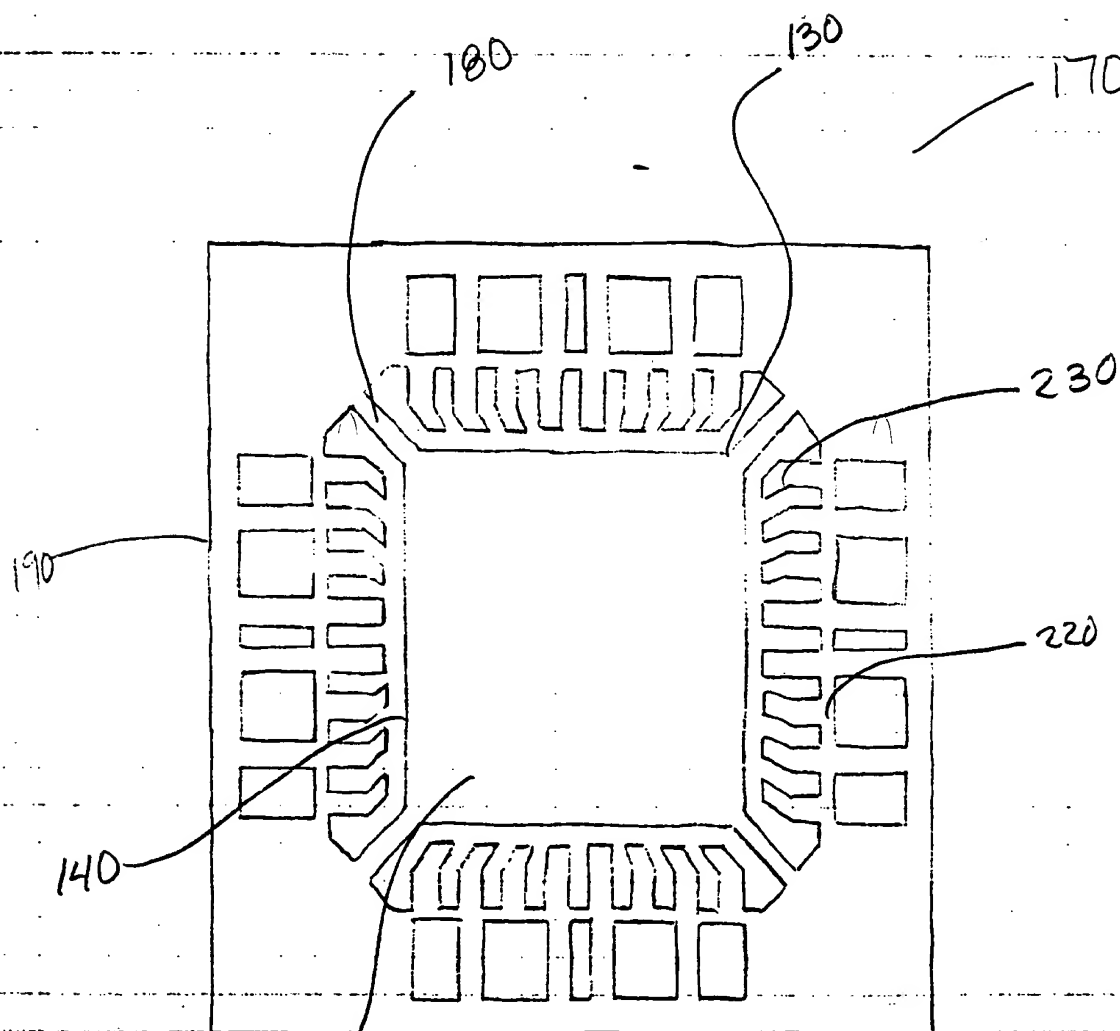


[illegible]

F16.3

Figure 1 consists of 12 sub-graphs labeled (a) through (l), each showing the growth of *E. coli* O157:H7 in ground beef under different conditions. The y-axis for all graphs is \log_{10} CFU/g, ranging from 0 to 10. The x-axis is time in hours, ranging from 0 to 120. The graphs show various growth curves, including control, heat treatment, and different chemical treatments.

- (a) Control: Shows a steady increase in bacterial count over time, reaching approximately 10 \log_{10} CFU/g by 120 hours.
- (b) Heat treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (c) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (d) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (e) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (f) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (g) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (h) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (i) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (j) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (k) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.
- (l) Chemical treatment: Shows a decrease in bacterial count over time, reaching approximately 5 \log_{10} CFU/g by 120 hours.



80

FIG. 4

↓
6

FIG. 5

A cross-sectional view of a semiconductor device 10. The device features a substrate 110 with a central channel 120. A gate stack 30 is positioned over the channel 120. The gate stack 30 includes a gate dielectric 270 and a gate electrode 260. The gate electrode 260 is connected to a gate terminal 235. The gate stack 30 is flanked by source/drain regions 262 and 264. The source/drain regions 262 and 264 are connected to source/drain terminals 230 and 235, respectively. The source/drain regions 262 and 264 are also connected to a source/drain electrode 280. The source/drain electrode 280 is connected to a source/drain terminal 235. The source/drain regions 262 and 264 are also connected to a source/drain electrode 280. The source/drain regions 262 and 264 are also connected to a source/drain electrode 280.
